# NCP5111

# High Voltage, High and Low Side Driver

The NCP5111 is a high voltage power gate driver providing two outputs for direct drive of 2 N−channel power MOSFETs or IGBTs arranged in a half−bridge configuration.

It uses the bootstrap technique to ensure a proper drive of the high−side power switch.

### Features

- High Voltage Range: up to 600 V
- dV/dt Immunity ±50 V/nsec
- Gate Drive Supply Range from 10 V to 20 V
- High and Low Drive Outputs
- Output Source / Sink Current Capability 250 mA / 500 mA
- 3.3 V and 5 V Input Logic Compatible
- Up to $V_{CC}$ Swing on Input Pins
- Extended Allowable Negative Bridge Pin Voltage Swing to −10 V for Signal Propagation
- Matched Propagation Delays between Both Channels
- One Input with Internal Fixed Dead Time (650 ns)
- Under $V_{CC}$ LockOut (UVLO) for Both Channels
- Pin−to−Pin Compatible with Industry Standards
- These are Pb−Free Devices

### Typical Applications

- Half−bridge Power Converters

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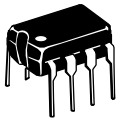
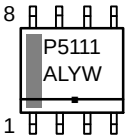
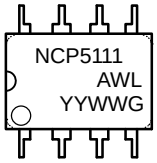
**SOIC−8**
**D SUFFIX**
**CASE 751**



**PDIP−8**
**P SUFFIX**
**CASE 626**

**MARKING DIAGRAMS**

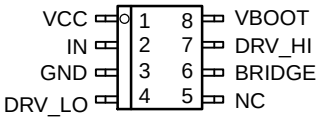



| | |
|---|---|
| NCP5111 | = Specific Device Code |
| A | = Assembly Location |
| L or WL | = Wafer Lot |
| Y or YY | = Year |
| W or WW | = Work Week |
| G or ▪ | = Pb−Free Package |

(Note: Microdot may be in either location)

**PINOUT INFORMATION**




**ORDERING INFORMATION**

| Device | Package | Shipping† |
|---|---|---|
| NCP5111PG | PDIP−8 (Pb−Free) | 50 Units / Rail |
| NCP5111DR2G | SOIC−8 (Pb−Free) | 2500 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

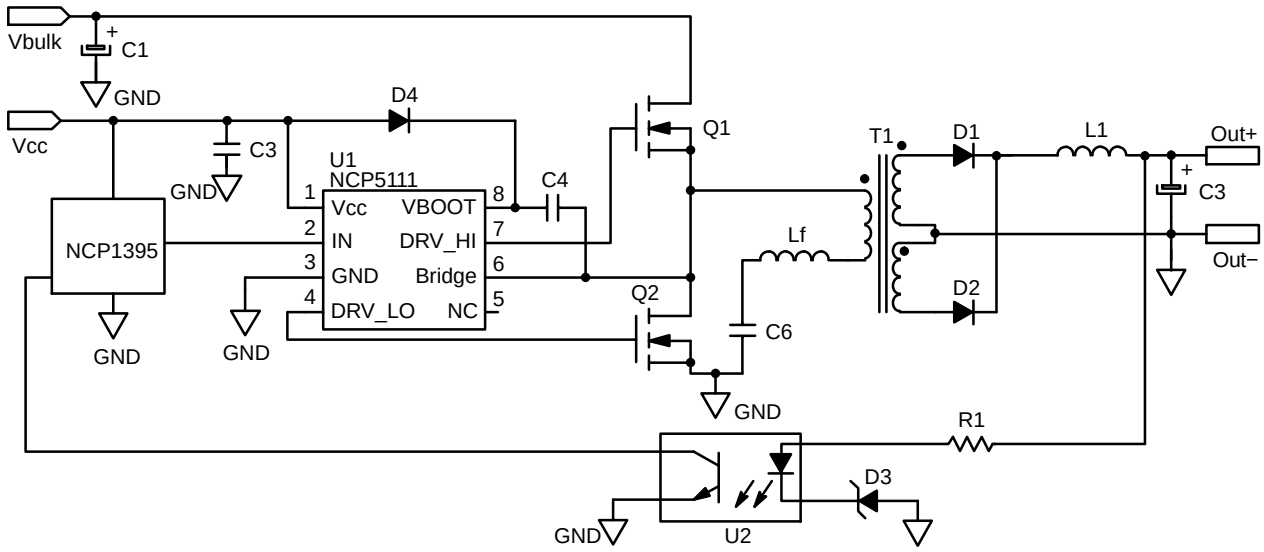



**Figure 1. Typical Application Resonant Converter (LLC type)**

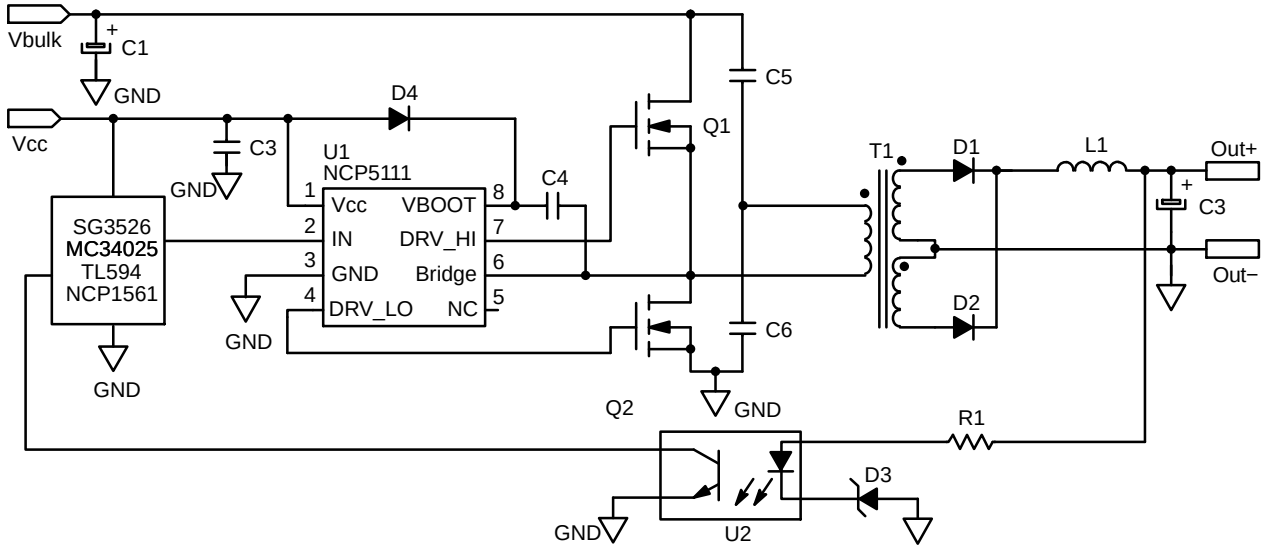



**Figure 2. Typical Application Half Bridge Converter**

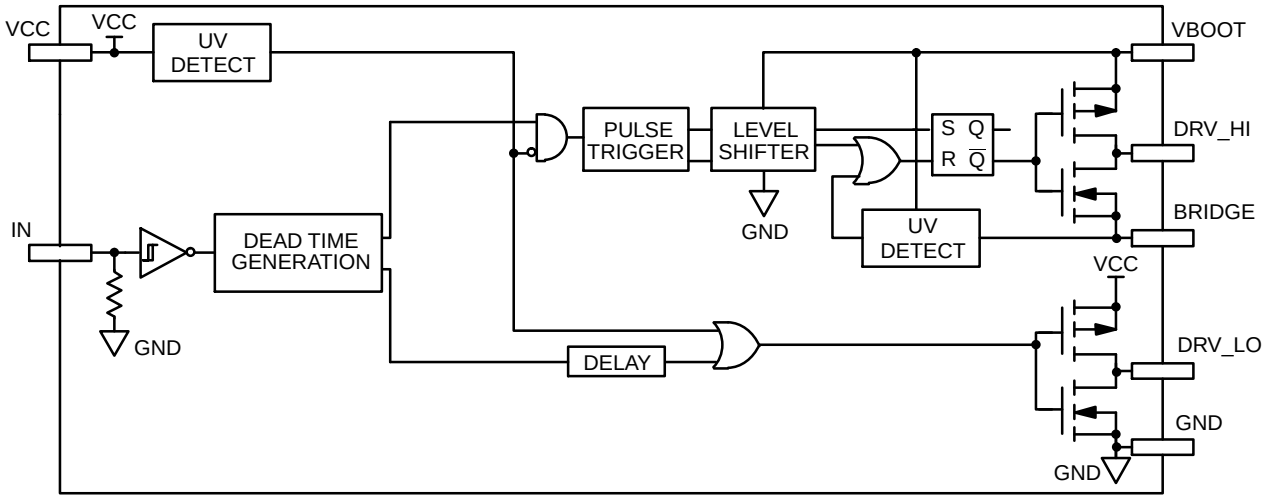



**Figure 3. Detailed Block Diagram**

## PIN DESCRIPTIONS

| Pin No. | Pin Name | Pin Function |
|---|---|---|
| 1 | VCC | Low side and main power supply |
| 2 | IN | Logic Input |
| 3 | GND | Ground |
| 4 | DRV_LO | Low side gate drive output |
| 5 | NC | Not Connected |
| 6 | BRIDGE | Bootstrap return or high side floating supply return |
| 7 | DRV_HI | High side gate drive output |
| 8 | VBOOT | Bootstrap power supply |

## MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|---|---|---|
| $V_{CC}$ | Main power supply voltage | −0.3 to 20 | V |
| $V_{CC\_transient}$ | Main transient power supply voltage:<br>$IV_{CC\_max}$ = 5 mA during 10 ms | 23 | V |
| $V_{BRIDGE}$ | VHV: High Voltage BRIDGE pin | −1 to 600 | V |
| $V_{BRIDGE}$ | Allowable Negative Bridge Pin Voltage for IN_LO Signal Propagation to DRV_LO | −10 | V |
| $V_{BOOT}$–$V_{BRIDGE}$ | VHV: Floating supply voltage | −0.3 to 20 | V |
| $V_{DRV\_HI}$ | VHV: High side output voltage | $V_{BRIDGE}$ − 0.3 to $V_{BOOT}$ + 0.3 | V |
| $V_{DRV\_LO}$ | Low side output voltage | −0.3 to $V_{CC}$ + 0.3 | V |
| $dV_{BRIDGE}/dt$ | Allowable output slew rate | 50 | V/ns |
| $V_{IN}$ | Inputs IN | −1.0 to $V_{CC}$ + 0.3 | V |
| | ESD Capability:<br>− HBM model (all pins except pins 6−7−8)<br>− Machine model (all pins except pins 6−7−8) | <br>2<br><br>200 | <br>kV<br><br>V |
| | Latchup capability per JEDEC JESD78 | | |
| $R_{\theta JA}$ | Power dissipation and Thermal characteristics<br>PDIP−8: Thermal Resistance, Junction−to−Air<br>SO−8: Thermal Resistance, Junction−to−Air | <br>100<br>178 | °C/W |
| $T_{STG}$ | Storage Temperature Range | −55 to +150 | °C |
| $T_{J\_max}$ | Maximum Operating Junction Temperature | +150 | °C |

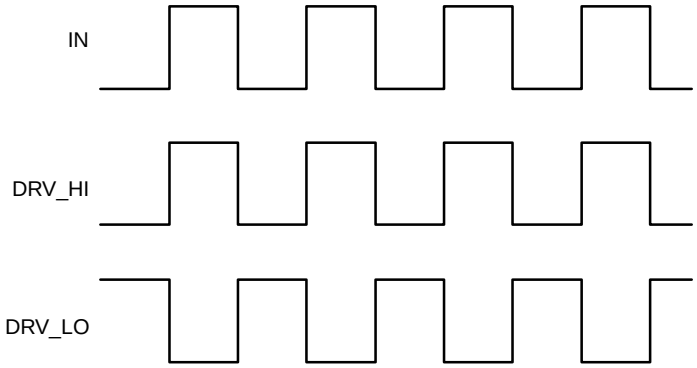
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

**ELECTRICAL CHARACTERISTIC** ($V_{CC}$ = $V_{boot}$ = 15 V, $V_{GND}$ = $V_{bridge}$, −40°C < $T_J$ < 125°C, Outputs loaded with 1 nF)

| Rating | Symbol | $T_J$ −40°C to 125°C | | | Units |
|---|---|---|---|---|---|
| | | Min | Typ | Max | |
| **OUTPUT SECTION** | | | | | |
| Output high short circuit pulsed current $V_{DRV}$ = 0 V, PW ≤ 10 μs (Note 1) | $I_{DRVsource}$ | − | 250 | − | mA |
| Output low short circuit pulsed current $V_{DRV}$ = Vcc, PW ≤ 10 μs (Note 1) | $I_{DRVsink}$ | − | 500 | − | mA |
| Output resistor (Typical value @ 25°C) Source | $R_{OH}$ | − | 30 | 60 | Ω |
| Output resistor (Typical value @ 25°C) Sink | $R_{OL}$ | − | 10 | 20 | Ω |
| High level output voltage, $V_{BIAS}$−$V_{DRV\_XX}$ @ $I_{DRV\_XX}$ = 20 mA | $V_{DRV\_H}$ | − | 0.7 | 1.6 | V |
| Low level output voltage $V_{DRV\_XX}$ @ $I_{DRV\_XX}$ = 20 mA | $V_{DRV\_L}$ | − | 0.2 | 0.6 | V |
| **DYNAMIC OUTPUT SECTION** | | | | | |
| Turn−on propagation delay (Vbridge = 0 V) (Note 2) | $t_{ON}$ | − | 750 | 1170 | ns |
| Turn−off propagation delay (Vbridge = 0 V or 50 V) (Notes 2 and 3) | $t_{OFF}$ | − | 100 | 170 | ns |
| Output voltage rise time (from 10% to 90% @ Vcc = 15 V) with 1 nF load | tr | − | 85 | 160 | ns |
| Output voltage fall time (from 90% to 10% @$V_{CC}$ = 15 V) with 1 nF load | tf | − | 35 | 75 | ns |
| Propagation delay matching between the High side and the Low side @ 25°C (Note 4) | Δt | − | 30 | 60 | ns |
| Internal fixed dead time (Note 5) | DT | 400 | 650 | 1000 | ns |
| **INPUT SECTION** | | | | | |
| Low level input voltage threshold | $V_{IN}$ | − | − | 0.8 | V |
| Input pull−down resistor ($V_{IN}$ < 0.5 V) | $R_{IN}$ | − | 200 | − | kΩ |
| High level input voltage threshold | $V_{IN}$ | 2.3 | − | − | V |
| Logic “1” input bias current @ $V_{IN}$ = 5 V @ 25°C | $I_{IN+}$ | − | 5 | 25 | μA |
| Logic “0” input bias current @ $V_{IN}$ = 0 V @ 25°C | $I_{IN−}$ | − | − | 2.0 | μA |
| **SUPPLY SECTION** | | | | | |
| Vcc UV Start−up voltage threshold | Vcc_stup | 8.0 | 8.9 | 9.9 | V |
| Vcc UV Shut−down voltage threshold | Vcc_shtdwn | 7.3 | 8.2 | 9.1 | V |
| Hysteresis on Vcc | Vcc_hyst | 0.3 | 0.7 | − | V |
| Vboot Start−up voltage threshold reference to bridge pin (Vboot_stup = Vboot − Vbridge) | Vboot_stup | 8.0 | 8.9 | 9.9 | V |
| Vboot UV Shut−down voltage threshold | Vboot_shtdwn | 7.3 | 8.2 | 9.1 | V |
| Hysteresis on Vboot | Vboot_shtdwn | 0.3 | 0.7 | − | V |
| Leakage current on high voltage pins to GND ($V_{BOOT}$ = $V_{BRIDGE}$ = DRV_HI = 600 V) | $I_{HV\_LEAK}$ | − | 5 | 40 | μA |
| Consumption in active mode (Vcc = Vboot, fsw = 100 kHz and 1 nF load on both driver outputs) | ICC1 | − | 4 | 5 | mA |
| Consumption in inhibition mode (Vcc = Vboot) | ICC2 | − | 250 | 400 | μA |
| Vcc current consumption in inhibition mode | ICC3 | − | 200 | − | μA |
| Vboot current consumption in inhibition mode | ICC4 | − | 50 | − | μA |

1. Parameter guaranteed by design.
2. $T_{ON}$ = $T_{OFF}$ + DT.
3. Turn−off propagation delay @ Vbridge = 600 V is guaranteed by design.
4. See characterization curve for Δt parameters variation on the full range temperature.
5. Timing diagram definition see: Figure 5 and Figure 6.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.




Note: DRV_HI output is in phase with the input.

**Figure 4. Input/Output Timing Diagram**

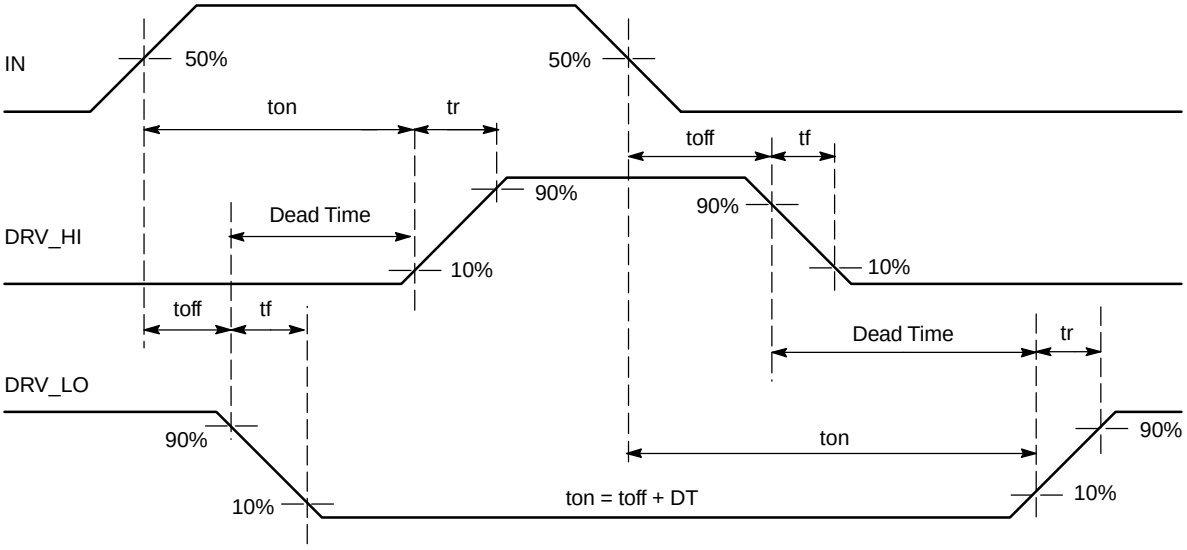



**Figure 5. Timing Definitions**

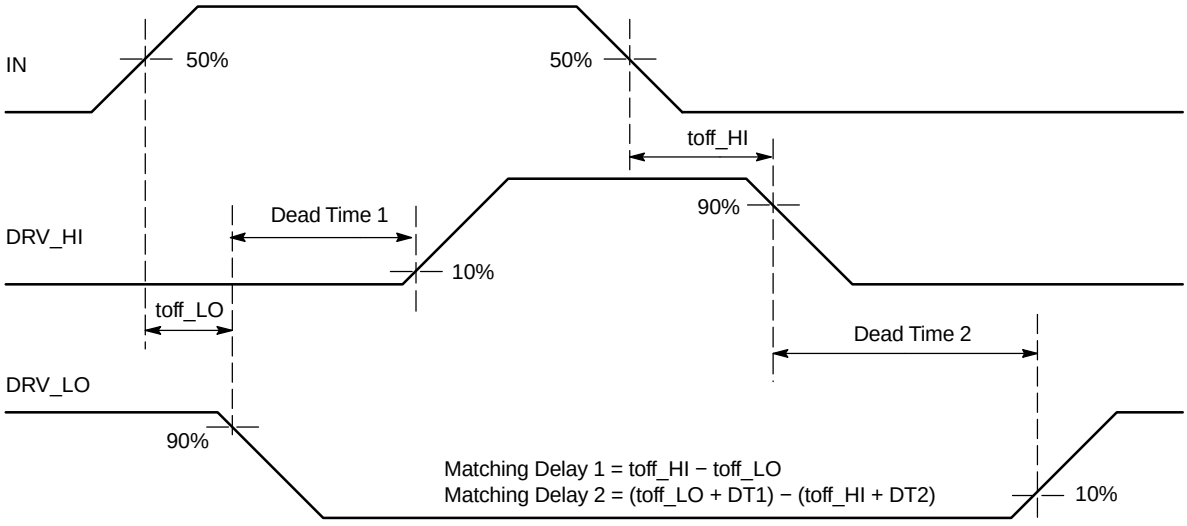



**Figure 6. Matching Propagation Delay**

## CHARACTERIZATION CURVES

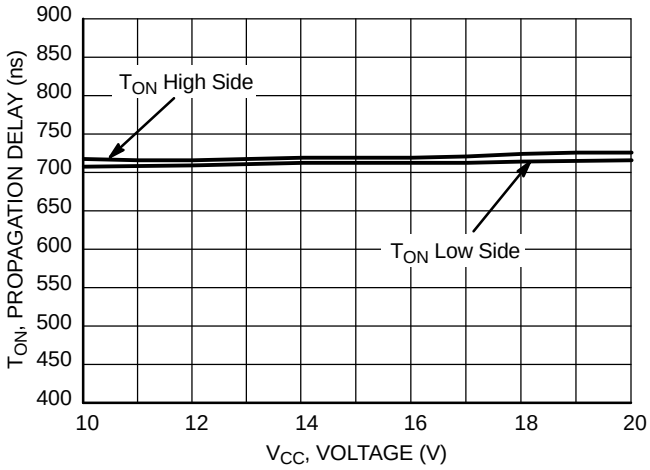



**Figure 7. Turn ON Propagation Delay vs. Supply Voltage ($V_{CC}$ = $V_{BOOT}$)**

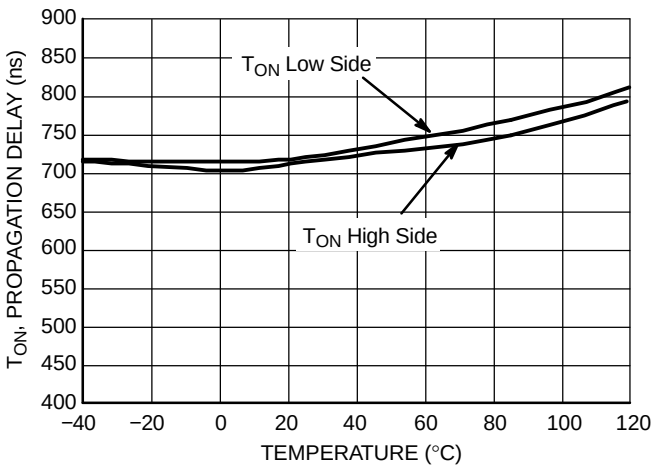



**Figure 8. Turn ON Propagation Delay vs. Temperature**

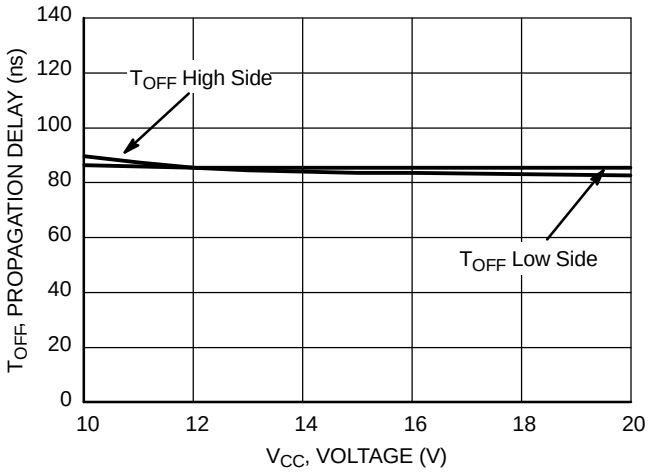



**Figure 9. Turn OFF Propagation Delay vs. Supply Voltage ($V_{CC}$ = $V_{BOOT}$)**

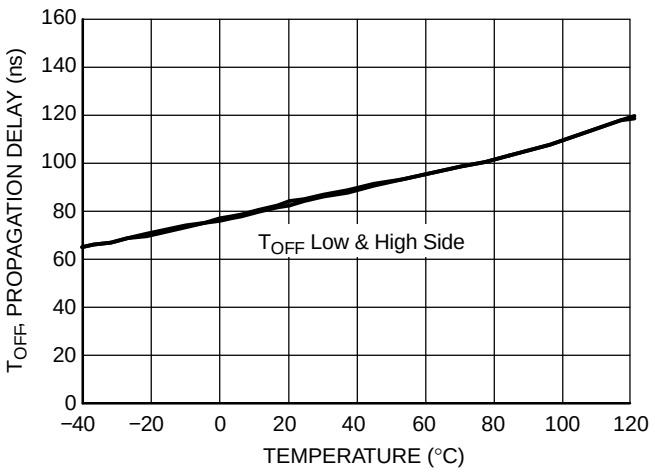



**Figure 10. Turn OFF Propagation Delay vs. Temperature**

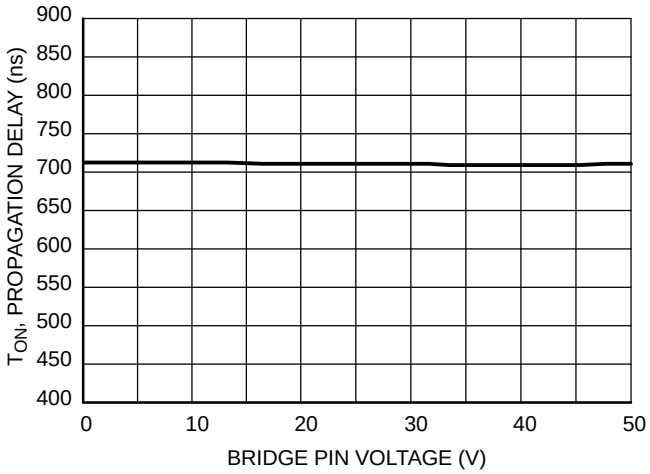



**Figure 11. High Side Turn ON Propagation Delay vs. VBRIDGE Voltage**

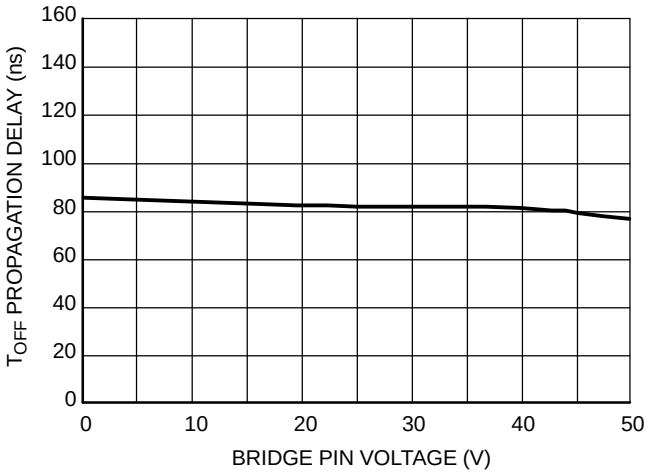



**Figure 12. High Side Turn OFF Propagation Delay vs. VBRIDGE Voltage**

## CHARACTERIZATION CURVES

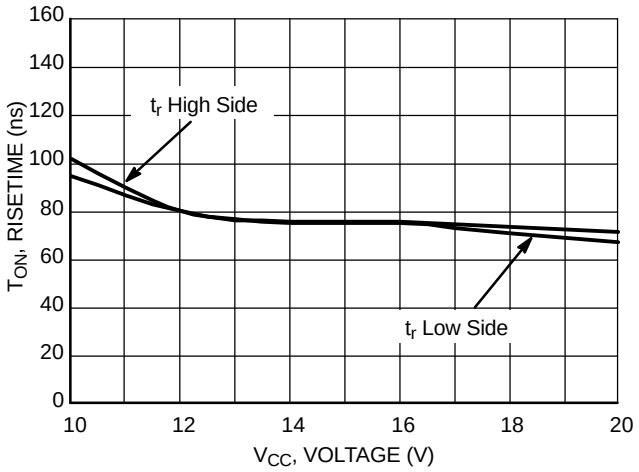



**Figure 13. Turn ON Risetime vs. Supply Voltage ($V_{CC}$ = $V_{BOOT}$)**

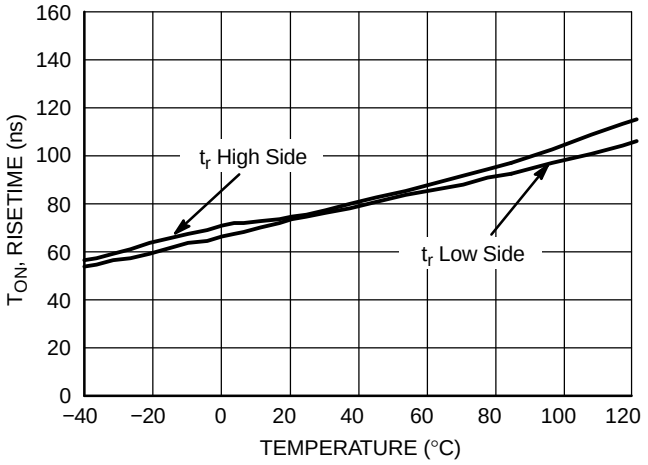



**Figure 14. Turn ON Risetime vs. Temperature**

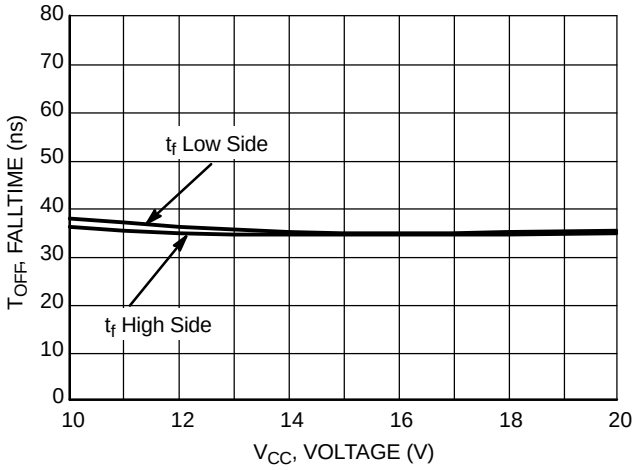



**Figure 15. Turn OFF Falltime vs. Supply Voltage ($V_{CC}$ = $V_{BOOT}$)**

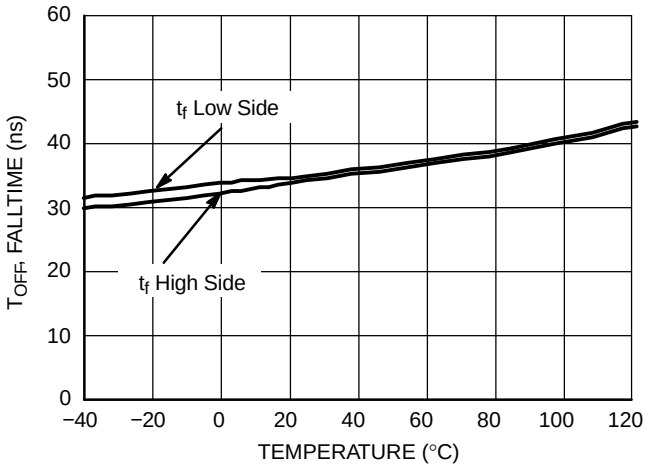



**Figure 16. Turn OFF Falltime vs. Temperature**

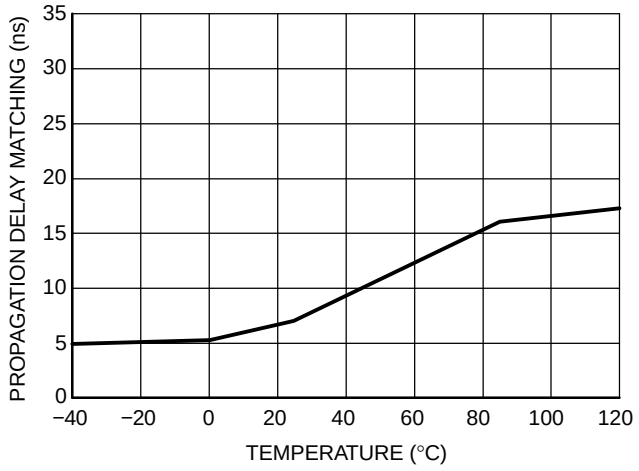



**Figure 17. Propagation Delay Matching Between High Side and Low Side Driver vs. Temperature**

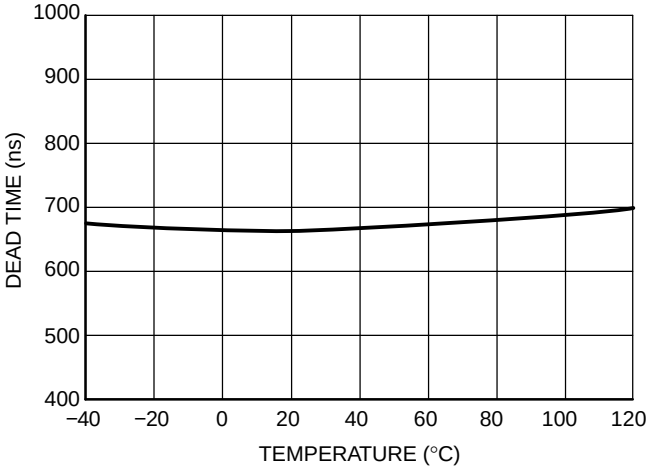



**Figure 18. Dead Time vs. Temperature**

## CHARACTERIZATION CURVES

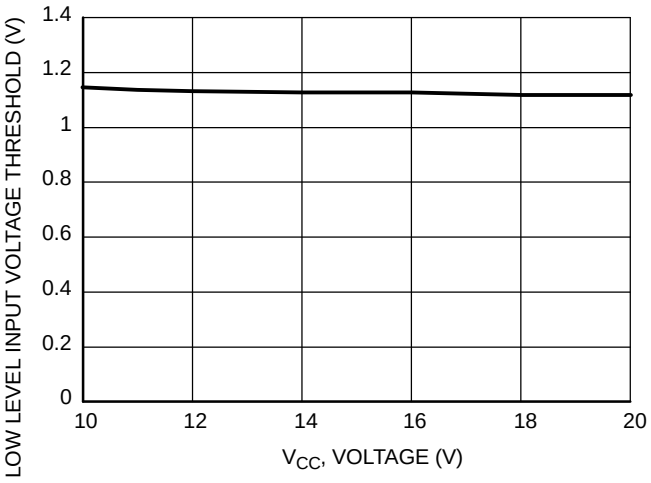



**Figure 19. Low Level Input Voltage Threshold vs. Supply Voltage ($V_{CC}$ = $V_{BOOT}$)**

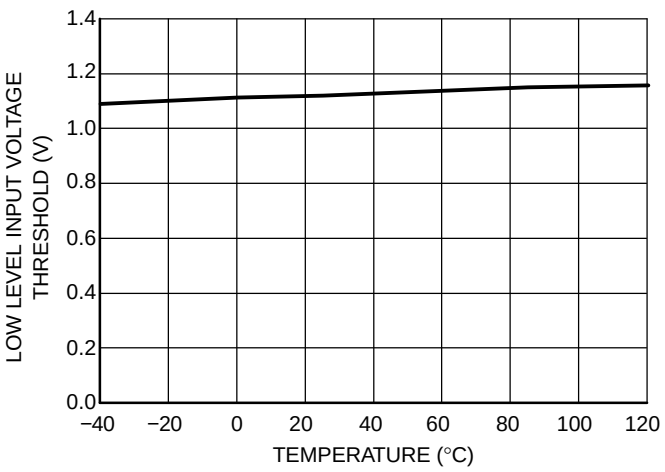



**Figure 20. Low Level Input Voltage Threshold vs. Temperature**

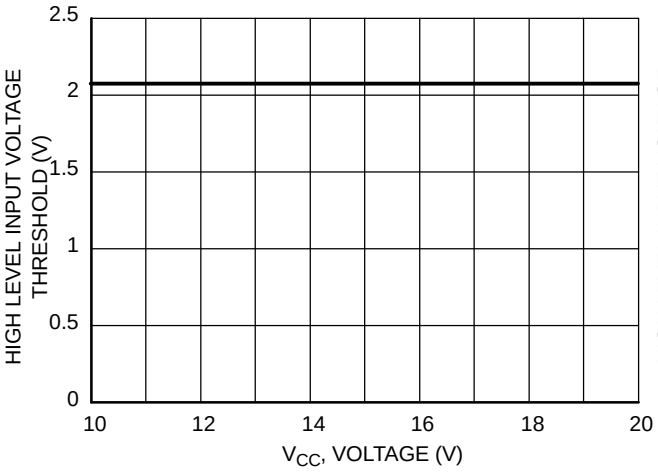



**Figure 21. High Level Input Voltage Threshold vs. Supply Voltage ($V_{CC}$ = $V_{BOOT}$)**

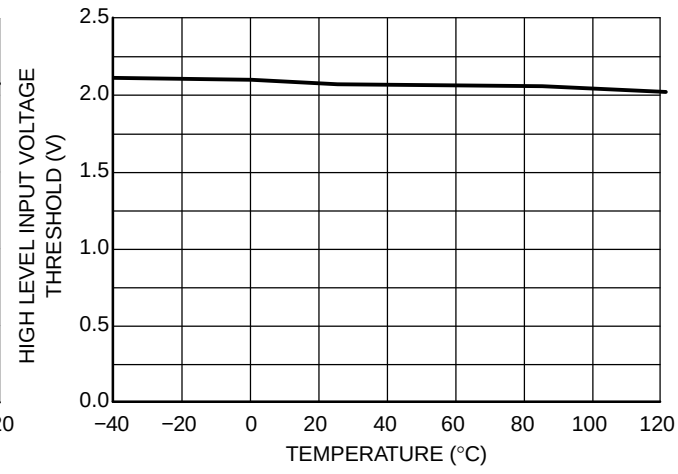



**Figure 22. High Level Input Voltage Threshold vs. Temperature**

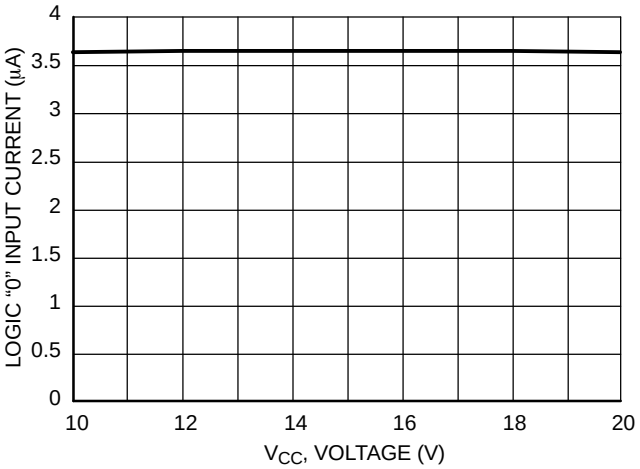



**Figure 23. Logic “0” Input Current vs. Supply Voltage ($V_{CC}$ = $V_{BOOT}$)**

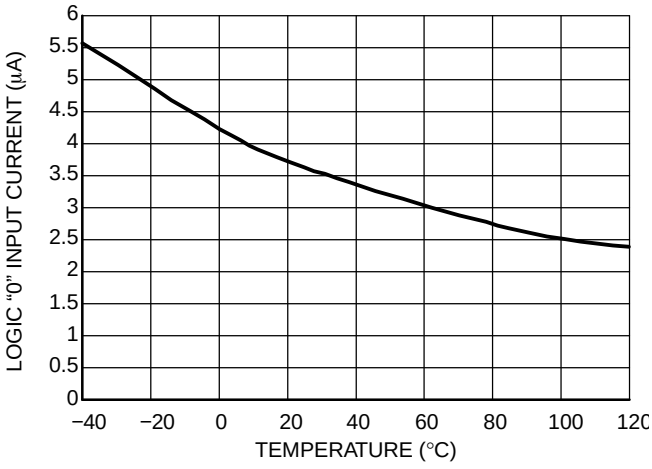



**Figure 24. Logic “0” Input Current vs. Temperature**

## CHARACTERIZATION CURVES

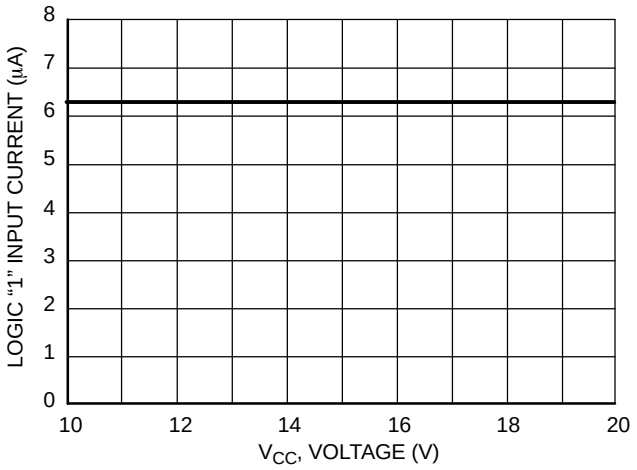



**Figure 25. Logic “1” Input Current vs. Supply Voltage ($V_{CC}$ = $V_{BOOT}$)**

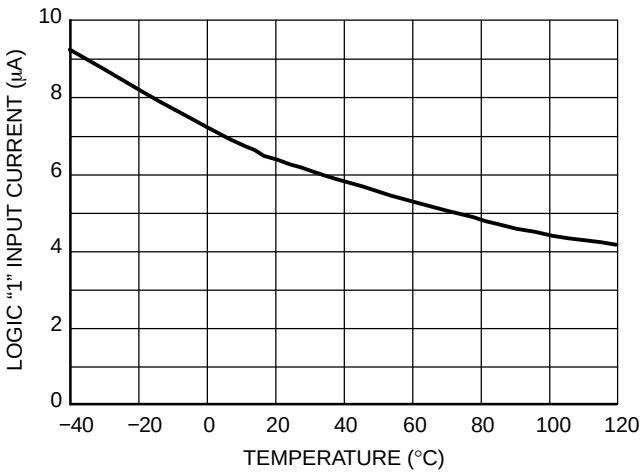



**Figure 26. Logic “1” Input Current vs. Temperature**

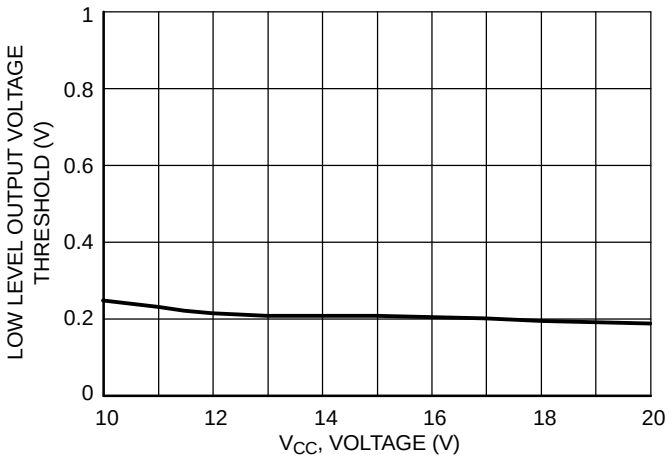



**Figure 27. Low Level Output Voltage vs. Supply Voltage ($V_{CC}$ = $V_{BOOT}$)**

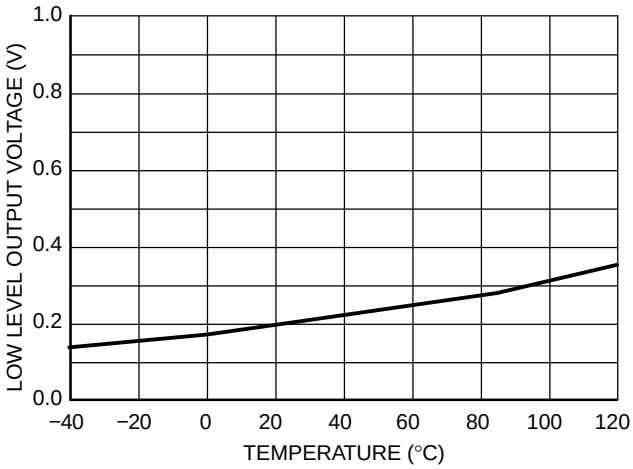



**Figure 28. Low Level Output Voltage vs. Temperature**

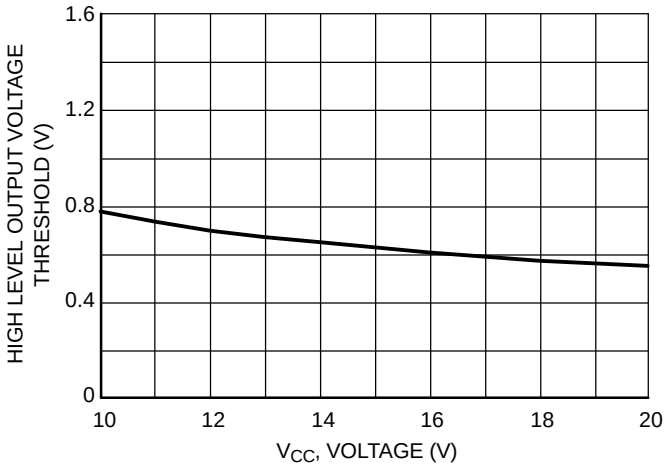



**Figure 29. High Level Output Voltage vs. Supply Voltage ($V_{CC}$ = $V_{BOOT}$)**

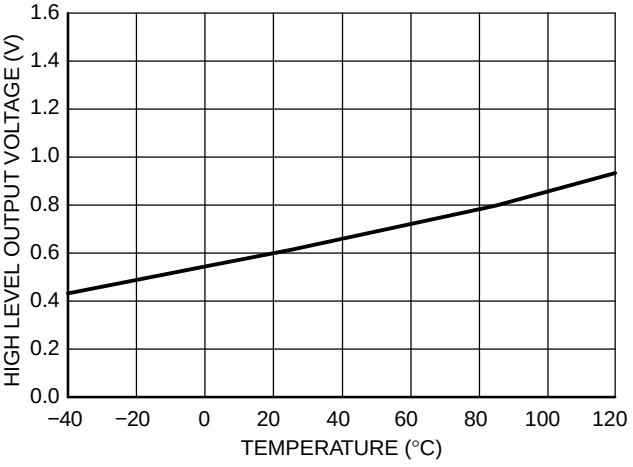



**Figure 30. High Level Output Voltage vs. Temperature**

## CHARACTERIZATION CURVES

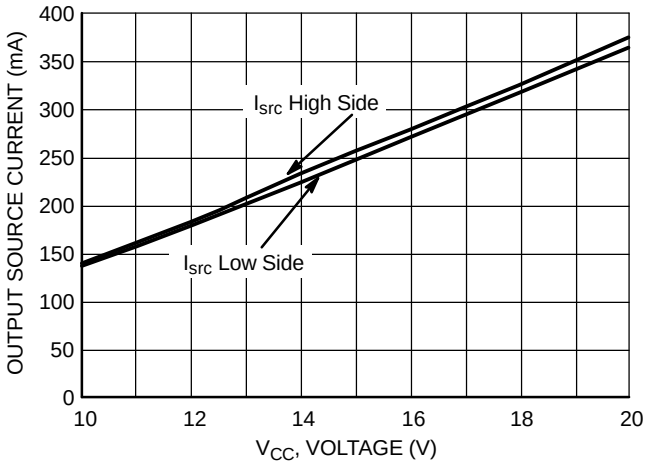



**Figure 31. Output Source Current vs. Supply Voltage ($V_{CC}$ = $V_{BOOT}$)**

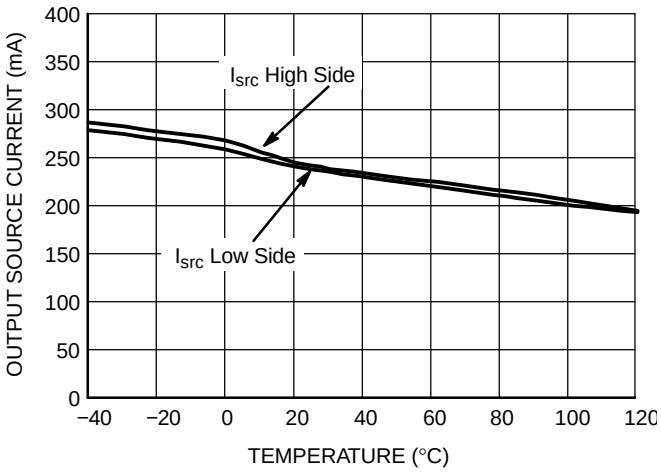



**Figure 32. Output Source Current vs. Temperature**

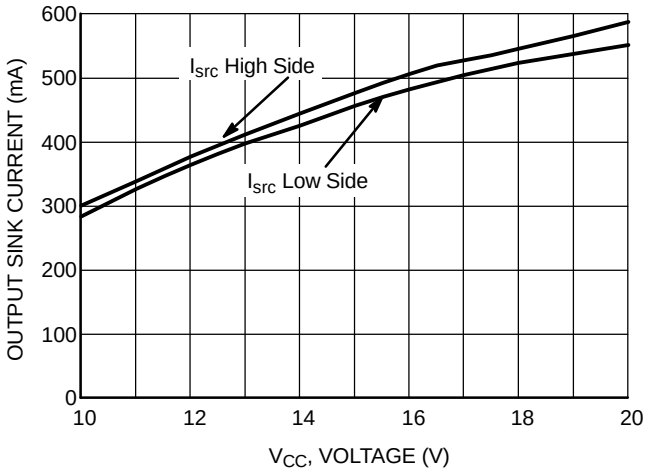



**Figure 33. Output Sink Current vs. Supply Voltage ($V_{CC}$ = $V_{BOOT}$)**

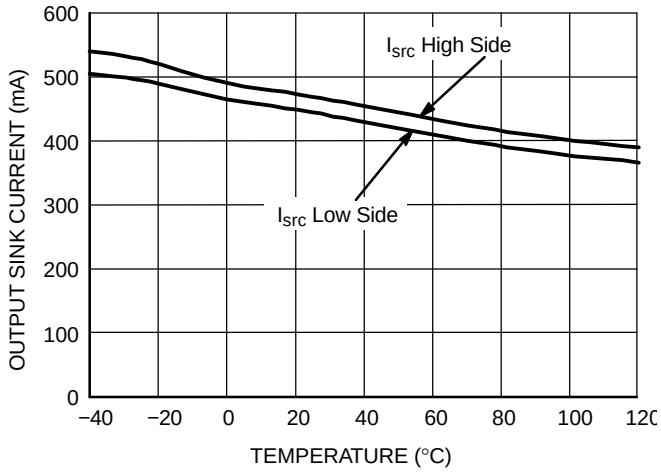



**Figure 34. Output Sink Current vs. Temperature**

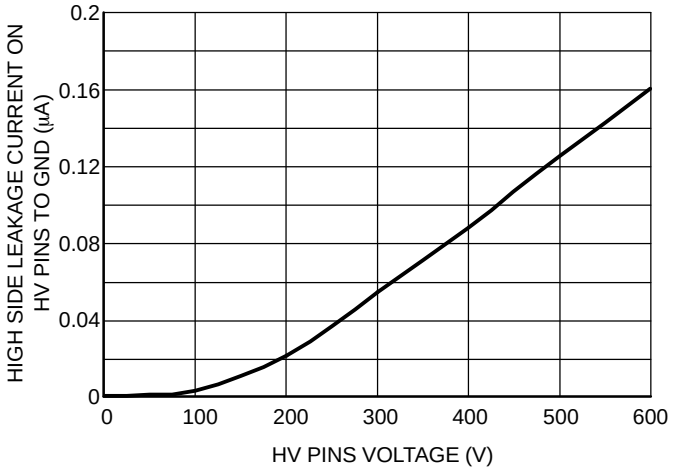



**Figure 35. Leakage Current on High Voltage Pins (600 V) to Ground vs. $V_{BRIDGE}$ Voltage ($V_{BRIGDE}$ = $V_{BOOT}$ = VDRV_HI)**

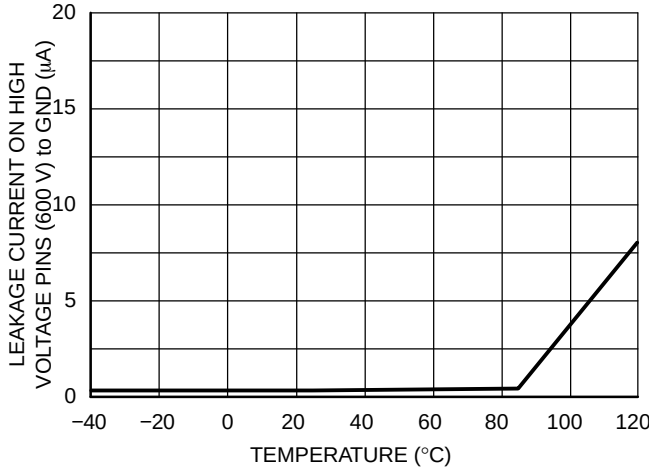



**Figure 36. Leakage Current on High Voltage Pins (600 V) to Ground vs. Temperature (VBRIDGE = $V_{BOOT}$ = VDRV_HI = 600 V)**

## CHARACTERIZATION CURVES

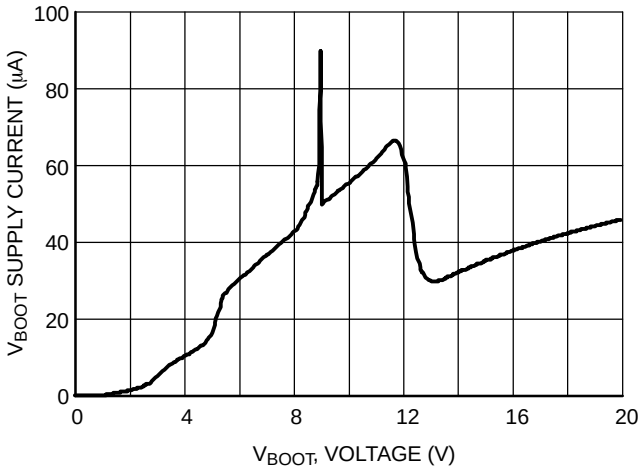



**Figure 37. $V_{BOOT}$ Supply Current vs. Bootstrap Supply Voltage**

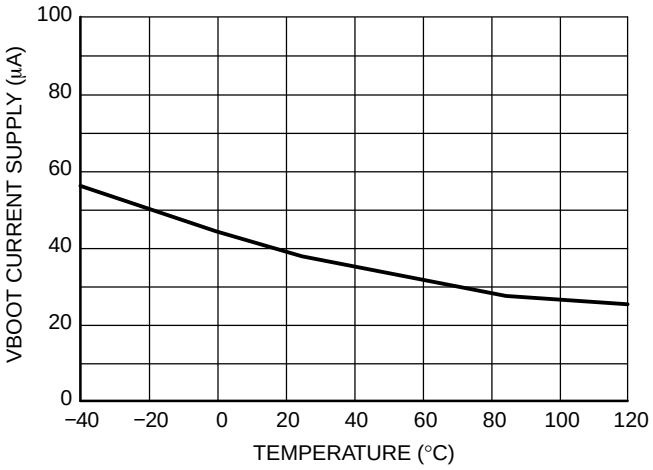



**Figure 38. $V_{BOOT}$ Supply Current vs. Temperature**

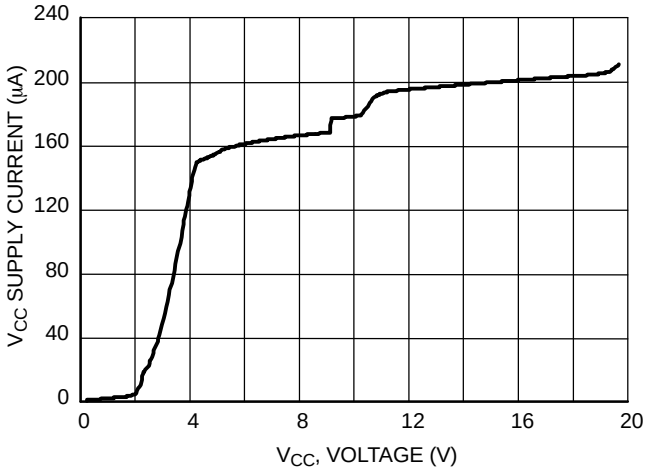



**Figure 39. $V_{CC}$ Supply Current vs. $V_{CC}$ Supply Voltage**

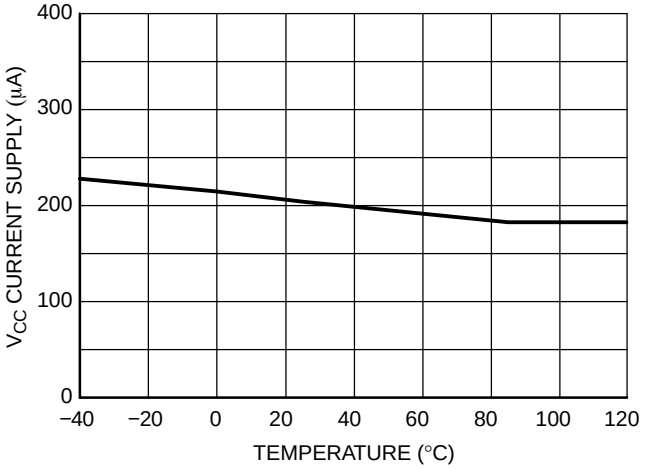



**Figure 40. $V_{CC}$ Supply Current vs. Temperature**

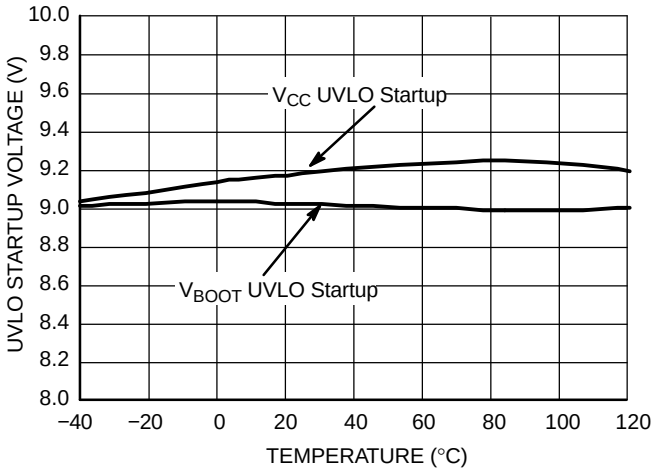



**Figure 41. UVLO Startup Voltage vs. Temperature**

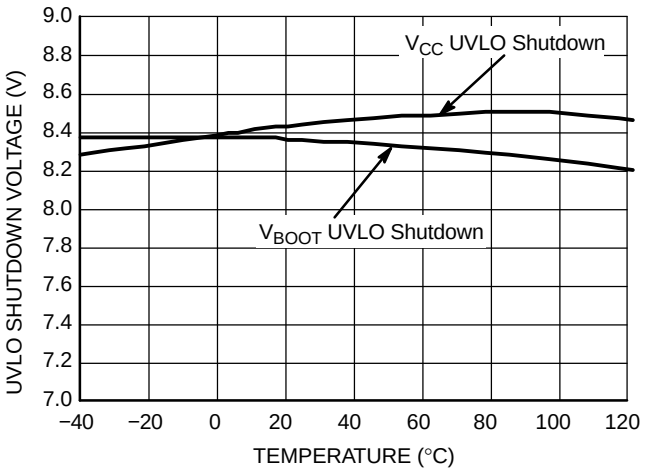



**Figure 42. UVLO Shutdown Voltage vs. Temperature**

## CHARACTERIZATION CURVES

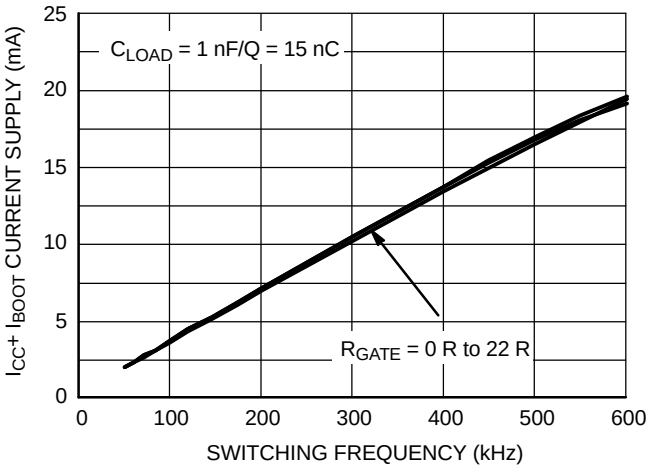



**Figure 43. $I_{CC1}$ Consumption vs. Switching Frequency with 15 nC Load on Each Driver @ $V_{CC}$ = 15 V**

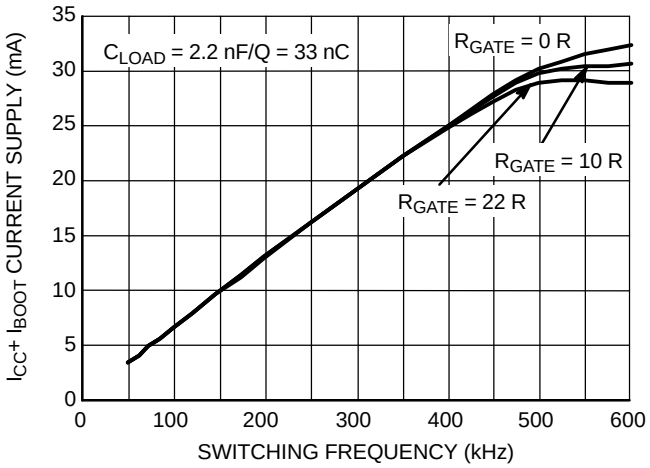



**Figure 44. $I_{CC1}$ Consumption vs. Switching Frequency with 33 nC Load on Each Driver @ $V_{CC}$ = 15 V**

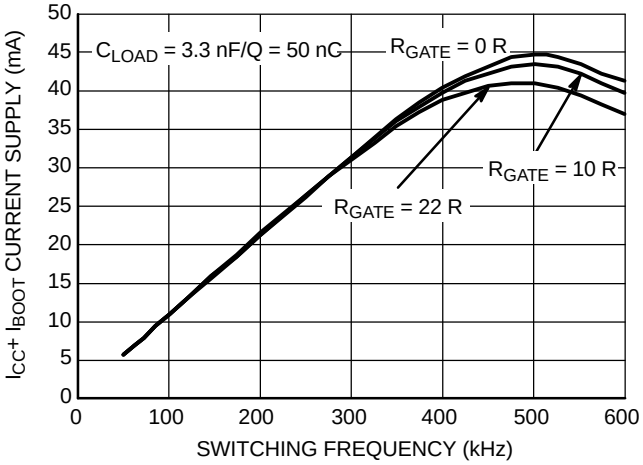



**Figure 45. $I_{CC1}$ Consumption vs. Switching Frequency with 50 nC Load on Each Driver @ $V_{CC}$ = 15 V**

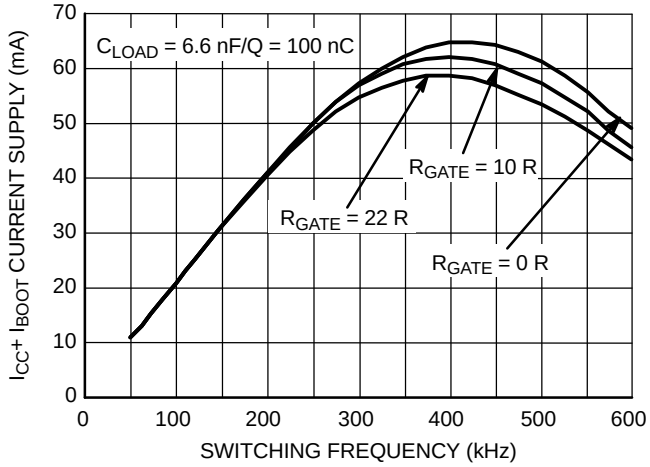



**Figure 46. $I_{CC1}$ Consumption vs. Switching Frequency with 100 nC Load on Each Driver @ $V_{CC}$ = 15 V**

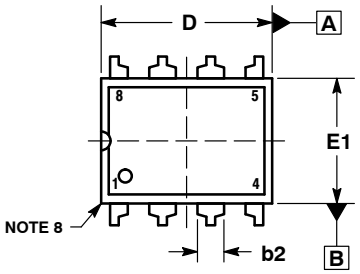
# MECHANICAL CASE OUTLINE
## PACKAGE DIMENSIONS

ON Semiconductor®

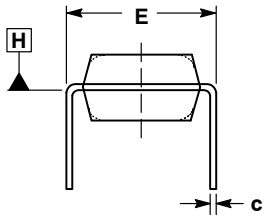
SCALE 1:1

**PDIP–8**
CASE 626–05
ISSUE P

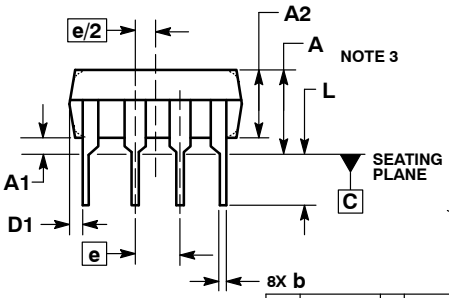
DATE 22 APR 2015



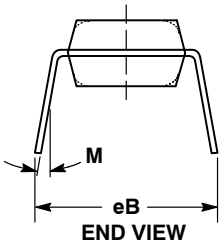

TOP VIEW




END VIEW
WITH LEADS CONSTRAINED
NOTE 5




SIDE VIEW



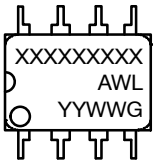

END VIEW
NOTE 6

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACKAGE SEATED IN JEDEC SEATING PLANE GAUGE GS–3.
4. DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
5. DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
7. DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
8. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

| | INCHES | | MILLIMETERS | |
|---|---|---|---|---|
| DIM | MIN | MAX | MIN | MAX |
| A | ---- | 0.210 | --- | 5.33 |
| A1 | 0.015 | ---- | 0.38 | --- |
| A2 | 0.115 | 0.195 | 2.92 | 4.95 |
| b | 0.014 | 0.022 | 0.35 | 0.56 |
| b2 | 0.060 TYP | | 1.52 TYP | |
| C | 0.008 | 0.014 | 0.20 | 0.36 |
| D | 0.355 | 0.400 | 9.02 | 10.16 |
| D1 | 0.005 | ---- | 0.13 | --- |
| E | 0.300 | 0.325 | 7.62 | 8.26 |
| E1 | 0.240 | 0.280 | 6.10 | 7.11 |
| e | 0.100 BSC | | 2.54 BSC | |
| eB | ---- | 0.430 | --- | 10.92 |
| L | 0.115 | 0.150 | 2.92 | 3.81 |
| M | ---- | 10° | --- | 10° |

STYLE 1:
PIN 1. AC IN
2. DC + IN
3. DC – IN
4. AC IN
5. GROUND
6. OUTPUT
7. AUXILIARY
8. $V_{CC}$

### GENERIC MARKING DIAGRAM*




XXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
YY = Year
WW = Work Week
G = Pb–Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, “G” or microdot “ ▪”, may or may not be present.

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|---|---|---|
| DESCRIPTION: | PDIP–8 | PAGE 1 OF 1 |

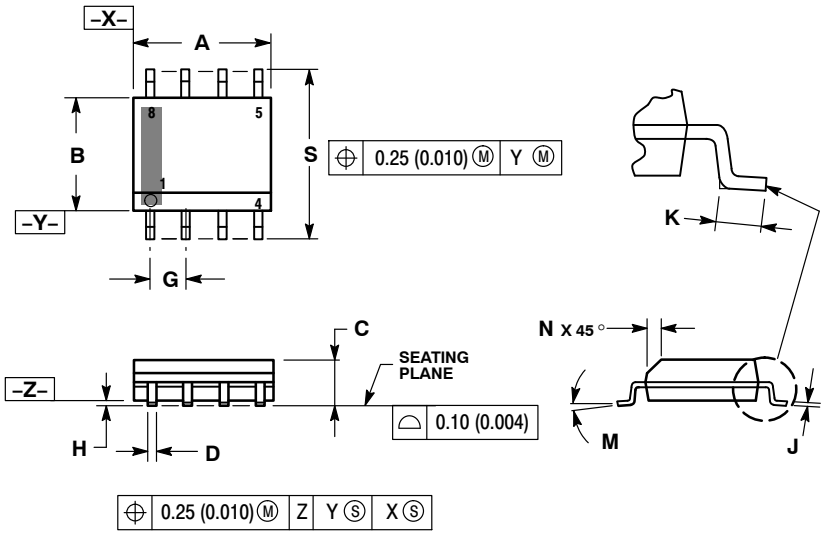
# MECHANICAL CASE OUTLINE
## PACKAGE DIMENSIONS

ON Semiconductor®

**SCALE 1:1**

**SOIC−8 NB**
CASE 751−07
ISSUE AK

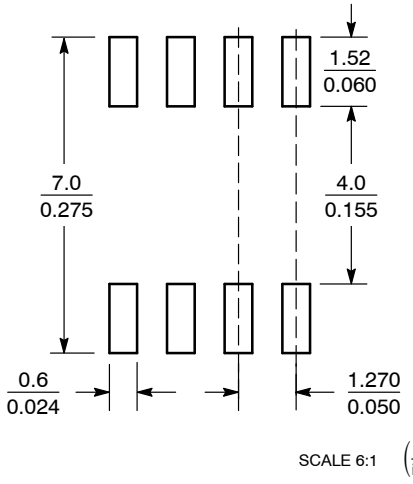
DATE 16 FEB 2011




NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

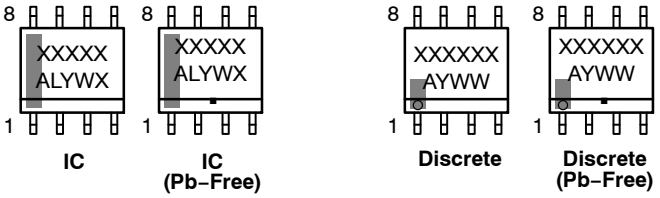
| | MILLIMETERS | | INCHES | |
|---|---|---|---|---|
| DIM | MIN | MAX | MIN | MAX |
| A | 4.80 | 5.00 | 0.189 | 0.197 |
| B | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.053 | 0.069 |
| D | 0.33 | 0.51 | 0.013 | 0.020 |
| G | 1.27 BSC | | 0.050 BSC | |
| H | 0.10 | 0.25 | 0.004 | 0.010 |
| J | 0.19 | 0.25 | 0.007 | 0.010 |
| K | 0.40 | 1.27 | 0.016 | 0.050 |
| M | 0° | 8° | 0° | 8° |
| N | 0.25 | 0.50 | 0.010 | 0.020 |
| S | 5.80 | 6.20 | 0.228 | 0.244 |

### SOLDERING FOOTPRINT*




*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### GENERIC MARKING DIAGRAM*




XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

**STYLES ON PAGE 2**

| | | | |
|---|---|---|---|
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| **DESCRIPTION:** | **SOIC−8 NB** | | **PAGE 1 OF 2** |

**SOIC−8 NB**
CASE 751−07
ISSUE AK

DATE 16 FEB 2011

STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. COLLECTOR
4. EMITTER
5. EMITTER
6. BASE
7. BASE
8. EMITTER

STYLE 2:
PIN 1. COLLECTOR, DIE, #1
2. COLLECTOR, #1
3. COLLECTOR, #2
4. COLLECTOR, #2
5. BASE, #2
6. EMITTER, #2
7. BASE, #1
8. EMITTER, #1

STYLE 3:
PIN 1. DRAIN, DIE #1
2. DRAIN, #1
3. DRAIN, #2
4. DRAIN, #2
5. GATE, #2
6. SOURCE, #2
7. GATE, #1
8. SOURCE, #1

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
7. ANODE
8. COMMON CATHODE

STYLE 5:
PIN 1. DRAIN
2. DRAIN
3. DRAIN
4. DRAIN
5. GATE
6. GATE
7. SOURCE
8. SOURCE

STYLE 6:
PIN 1. SOURCE
2. DRAIN
3. DRAIN
4. SOURCE
5. SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 7:
PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

STYLE 8:
PIN 1. COLLECTOR, DIE #1
2. BASE, #1
3. BASE, #2
4. COLLECTOR, #2
5. COLLECTOR, #2
6. EMITTER, #2
7. EMITTER, #1
8. COLLECTOR, #1

STYLE 9:
PIN 1. EMITTER, COMMON
2. COLLECTOR, DIE #1
3. COLLECTOR, DIE #2
4. EMITTER, COMMON
5. EMITTER, COMMON
6. BASE, DIE #2
7. BASE, DIE #1
8. EMITTER, COMMON

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT
4. GROUND
5. GROUND
6. BIAS 2
7. INPUT
8. GROUND

STYLE 11:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 12:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 14:
PIN 1. N−SOURCE
2. N−GATE
3. P−SOURCE
4. P−GATE
5. P−DRAIN
6. P−DRAIN
7. N−DRAIN
8. N−DRAIN

STYLE 15:
PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

STYLE 16:
PIN 1. EMITTER, DIE #1
2. BASE, DIE #1
3. EMITTER, DIE #2
4. BASE, DIE #2
5. COLLECTOR, DIE #2
6. COLLECTOR, DIE #2
7. COLLECTOR, DIE #1
8. COLLECTOR, DIE #1

STYLE 17:
PIN 1. VCC
2. V2OUT
3. V1OUT
4. TXE
5. RXE
6. VEE
7. GND
8. ACC

STYLE 18:
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 19:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

STYLE 20:
PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3
4. CATHODE 4
5. CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 22:
PIN 1. I/O LINE 1
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 23:
PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 24:
PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

STYLE 25:
PIN 1. VIN
2. N/C
3. REXT
4. GND
5. IOUT
6. IOUT
7. IOUT
8. IOUT

STYLE 26:
PIN 1. GND
2. dv/dt
3. ENABLE
4. ILIMIT
5. SOURCE
6. SOURCE
7. SOURCE
8. VCC

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

STYLE 28:
PIN 1. SW_TO_GND
2. DASIC_OFF
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBULK
7. VBULK
8. VIN

STYLE 29:
PIN 1. BASE, DIE #1
2. EMITTER, #1
3. BASE, #2
4. EMITTER, #2
5. COLLECTOR, #2
6. COLLECTOR, #2
7. COLLECTOR, #1
8. COLLECTOR, #1

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
3. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
6. SOURCE 1/DRAIN 2
7. SOURCE 1/DRAIN 2
8. GATE 1

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